

ERSO-87-076C



April 30, 2004

To: Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572
28 Davis Avenue
Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/812,735 03/30/04

Lai-Juh Chen

CHEMICAL MECHANICAL POLISH PROCESS
CONTROL METHOD USING THERMAL IMAGING
OF POLISHING PAD

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation
In An Application.

The following Patents and/or Publications are submitted to
comply with the duty of disclosure under CFR 1.97-1.99 and
37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being
deposited with the United States Postal Service as first class
mail in an envelope addressed to: Commissioner for Patents,
P.O. Box 1450, Alexandria, VA 22313-1450, on May 4, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date Stephen B. Ackerman 5/4/04

U.S. Patent 5,647,952 to Chen, "Chemical/Mechanical Polish (CMP) Endpoint Method," describes a method for endpoint detection in CMP in which infrared detection is used to measure the temperature of a selected polishing pad location which is abrading the surface of the semiconductor substrate.

U.S. Patent 5,234,868 to Cote, "Method for Determining Planarization Endpoint during Chemical-Mechanical Polishing," describes a monitor structure surrounded by a moat.

U.S. Patent 5,240,552 to Yu et al., "Chemical Mechanical Planarization (CMP) of a Semiconductor Wafer using Acoustical Waves for In-Situ End Point Detection," directs acoustical waves at the wafer during CMP and through analysis of the reflected wave form controls the planarization process.

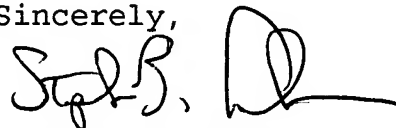
U.S. Patent 5,308,438 to Cote et al., "Endpoint Detection Apparatus and Method for Chemical/Mechanical Polishing," describes an endpoint detection method in which the power required to maintain a set rotational speed in a motor rotating the substrate is monitored.

U.S. Patent 5,337,015 to Lustig et al., "In-Situ Endpoint Detection Method and Apparatus for Chemical-Mechanical Polishing using Low Amplitude Input Voltage," utilizes electrodes built into the polishing pad, and a high frequency, low voltage signal, and detection means as a method for measuring the thickness of a dielectric layer being polished.

U.S. Patent 5,413,941 to Koos et al., "Optical End Point Detection Methods in Semiconductor Planarizing Polishing Processes," describes a method for endpoint detection for polishing by impinging laser light onto the substrate being polished and measuring the reflected light.

U.S. Patent 5,196,353 to Sandhu et al., "Method for Controlling a Semiconductor (CMP) Process by Measuring a Surface Temperature and Developing a Thermal Image of the Wafer," describes the use of infrared radiation detection to measure the surface temperature of a semiconductor wafer during a polishing process.

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman", followed by a large, stylized flourish or initial.

Stephen B. Ackerman,
Reg. No. 37761

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

MAY 06 2004

(Use separate sheets if necessary)

PIPE
 PATENT & TRADEMARK OFFICE

Document Number (Continued)

ERSD-87-076C

Application Number

10/812,735

Applicant

Lai-Juh Chen

Filing Date

03/30/04

Group Art Unit

U. S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	TITLE	CLASS	SUBCLASS	PLUNG DATE IF APPROPRIATE
	5647952	7/15/97	Chen	156	636.1	4/1/96
	5196353	3/23/93	Sandhu et al.	437	8	1/3/92
	5413941	5/9/95	Koos et al.	437	8	1/6/94
	5337015	8/9/94	Lustig et al.	324	671	6/14/93
	5308438	5/3/94	Cote et al.	156	636	1/30/92
	5240552	8/31/93	Yu et al.	156	636	12/11/91
	5234868	8/10/93	Cote	437	225	10/29/92

FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
					YES	NO

OTHER DOCUMENTS (Including Author, Title, Date, Portmox Pages, Etc.)

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.